Serial No. Attorney Docket No. 09/532,915 SEL 170 <u>Applicant</u> LIST OF PUBLICATIO Masahiko HAYAKAWA et al CITED BY APPLICANT Filing Date Group March 22, 2000 2811 U.S. PATENT DOCUMENTS SUB-FILING \*EXAMINER DOCUMENT INITIAL NUMBER DATE NAME CLASS CLASS DATE FOREIGN PATENT DOCUMENTS DOCUMENT SUB-FILING CLASS CLASS DATE NUMBER DATE NAME 10/24/96 JP 10-135469 05/22/98 Semiconductor Energy Laboratory Co., Ltd. OTHER PUBLICATIONS (Including Author, Title, Date, Pertinent Pages)

EXAMINER:

22, 1998.

DATE CONSIDERED:

10.02.01

\*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP form. Draw line through citation if not in conformance and not considered. Include a copy of this form with the next communication to applicant.

English abstract re Japanese patent application no. 10-135469, published May

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LIST OF PUBLICATIONS CITED BY APPLICANT	<u>Applicant</u> Masahiko HAYAKAWA et al	
	<u>Filing Date</u> March 22, 2000	<u>Group</u> 2811

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